



## Si4946BEY vs. Si4946EY

**Description:** Dual N-Channel, 60 V (D-S) MOSFET

**Package:** SO-8

**Pin Out:** Identical

**Part Number Replacements:**

Si4946BEY-T1-E3 Replaces Si4946EY-T1-E3

Si4946BEY-T1 Replaces Si4946EY-T1

<b>ABSOLUTE MAXIMUM RATINGS</b> $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted				
Parameter	Symbol	Si4946BEY	Si4946EY	Unit
Drain-Source Voltage	$V_{DS}$	60	60	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	$\pm 20$	
Continuous Drain Current	$T_A = 25\text{ }^\circ\text{C}$	$I_D$	5.3	A
	$T_A = 70\text{ }^\circ\text{C}$		4.4	
Pulsed Drain Current	$I_{DM}$	30	30	
Continuous Source Current (MOSFET Diode Conduction)	$I_S$	2	2	
Avalanche Current	$L = 0.1\text{ mH}$	$I_{AS}$	12	
Power Dissipation	$T_A = 25\text{ }^\circ\text{C}$	$P_D$	2.4	W
	$T_A = 70\text{ }^\circ\text{C}$		1.7	
Operating Junction and Storage Temperature Range	$T_j$ and $T_{stg}$	- 55 to 150	- 55 to 150	$^\circ\text{C}$
Maximum Junction-to-Ambient	$R_{thJA}$	62.5	62.5	$^\circ\text{C/W}$

<b>SPECIFICATIONS</b> $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted									
Parameter	Symbol	Si4946BEY			Si4946EY			Unit	
		Min	Typ	Max	Min	Typ	Max		
<b>Static</b>									
Gate-Threshold Voltage	$V_{GS(th)}$	1.0	2.4	3.0	1.0		3.0	V	
Gate-Body Leakage	$I_{GSS}$			$\pm 100$			$\pm 100$	nA	
Zero Gate Voltage Drain Current	$I_{DSS}$			1			1	$\mu\text{A}$	
On-State Drain Current	$V_{GS} = 10\text{ V}$	$I_{D(on)}$	30		20			A	
Drain-Source On-Resistance	$V_{GS} = 10\text{ V}$	$r_{DS(on)}$		0.033	0.041		0.045	0.055	$\Omega$
	$V_{GS} = 4.5\text{ V}$			0.041	0.052		0.055	0.075	
Forward Transconductance		$g_{fs}$		24			13	S	
Diode Forward Voltage		$V_{SD}$		0.8	1.2		0.9	1.2	V
<b>Dynamic</b>									
Total Gate Charge		$Q_g$		17	25		19	30	nC
Gate-Source Charge		$Q_{gs}$		3.3			4		
Gate-Drain Charge		$Q_{gd}$		3.7			3		
Gate Resistance		$R_g$	3.1	6.5	9.5	1		3.6	$\Omega$
<b>Switching</b>									
Turn-On Time <sup>a</sup>		$t_{d(on)}$		10	15		13	20	ns
		$t_r$		12	20		11	20	
Turn-Off Time <sup>a</sup>		$t_{d(off)}$		25	40		36	60	
		$t_f$		10	15		11	20	
Source-Drain Reverse Recovery Time		$t_{rr}$		25	50		35	60	

Notes:

a. Datasheet test conditions differ;  $R_L = 6.8\text{ }\Omega$ ,  $I_D = 4.4\text{ A}$ ,  $R_g = 1\text{ }\Omega$  on the Si4946BEY and  $R_L = 30\text{ }\Omega$ ,  $I_D = 1\text{ A}$ ,  $R_g = 6\text{ }\Omega$  on the Si4946EY.

Specification comparisons are supplied as a courtesy to compare two devices and do not constitute a commercial product datasheet or any guarantee of identical performance. Designers should refer to the appropriate datasheets of the same number for guaranteed specification limits.